

PNP General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 73.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units 🚿
V _{CES}	Collector-Emitter Voltage	80	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	4.0	V
lc	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
All voltages (V) and currents (A) are negative polarity for PNP transistors. WWW.100Y

Thermal Characteristics TA = 25°C unless otherwise noted

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Symbol	Characteristic	Max			Units
	W.100 *	MPSA56	*MMBTA56	**PZTA56	
PD	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/∘C
S ^{θJC}	Thermal Resistance, Junction to Case	83.3		W.10	°C/W
R _{0JA}	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

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PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS	W.100Y.COM.TW	W	WW.	00Y.C
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	80		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	80	NN.	V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \mu {\rm A}, I_{\rm C} = 0$	4.0	WW	V
CEO Collector-Cutoff Current		$V_{CE} = 60 \text{ V}, I_{B} = 0$		0.1	μA
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 80 \text{ V}, I_{E} = 0$		0.1	μA

V _{BE(on)}	Eddo Emiliar on Voliago		N			
Vpr(an)	Base-Emitter On Voltage	$I_{c} = 100 \text{ mA}, V_{cE} = 1.0 \text{ V}$		1.2	V	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$	1.1	0.25	V	
N _{FE}	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100 100	4	WWW.	

SMALL SIGNAL CHARACTERISTICS

f _T	Current Gain - Bandwidth Product	$I_{C} = 100 \text{ mA}, V_{CE} = 1.0 \text{ V},$ f = 100 MHz	50	W	MHz
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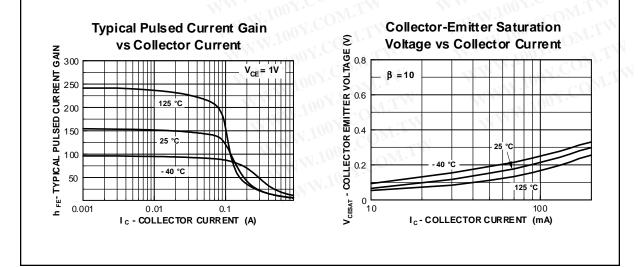
*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

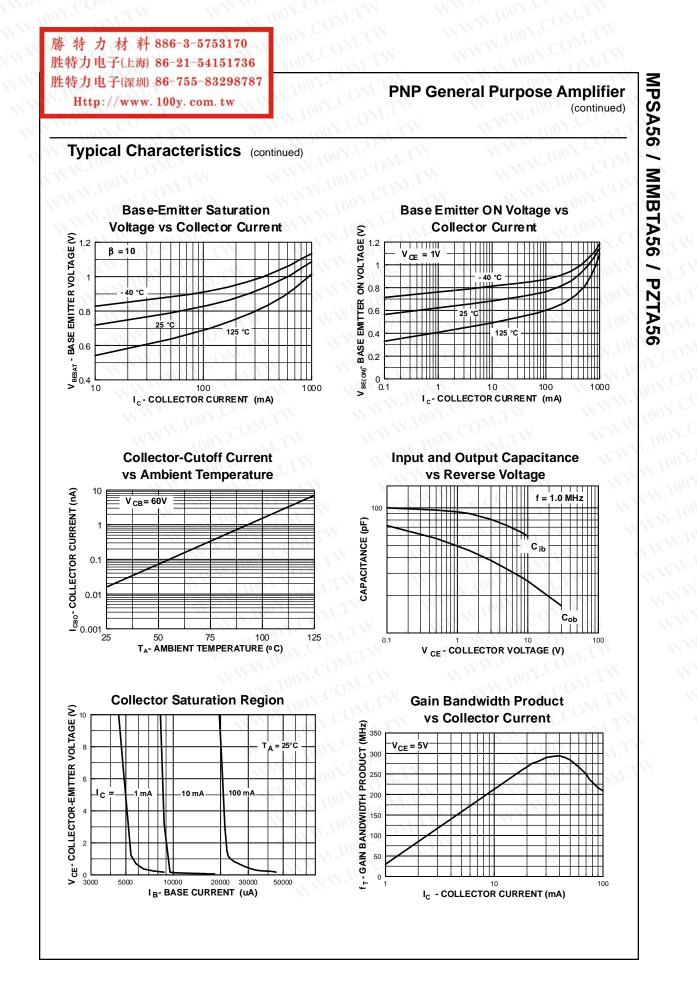
Spice Model

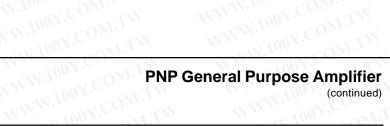
PNP (Is=12.27p Xti=3 Eg=1.11 Vaf=100 Bf=91.63 Ne=1.531 Ise=12.27p Ikf=1.009 Xtb=1.5 Br=1.287 Nc=2 Isc=0 Ikr=0 Rc=.6 Cjc=48.28p Mjc=.5615 Vjc=.75 Fc=.5 Cje=106.7p Mje=.5168 Vje=.75 Tr=496.3n Tf=865.8p Itf=.2 Vtf=2 Xtf=.8 Rb=10)

Typical Characteristics



MPSA56 / MMBTA56 / PZTA56





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Typical Characteristics (continued)

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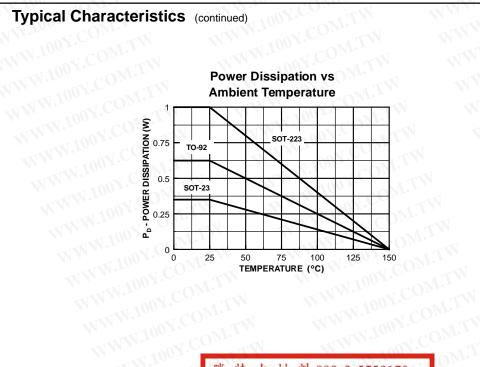
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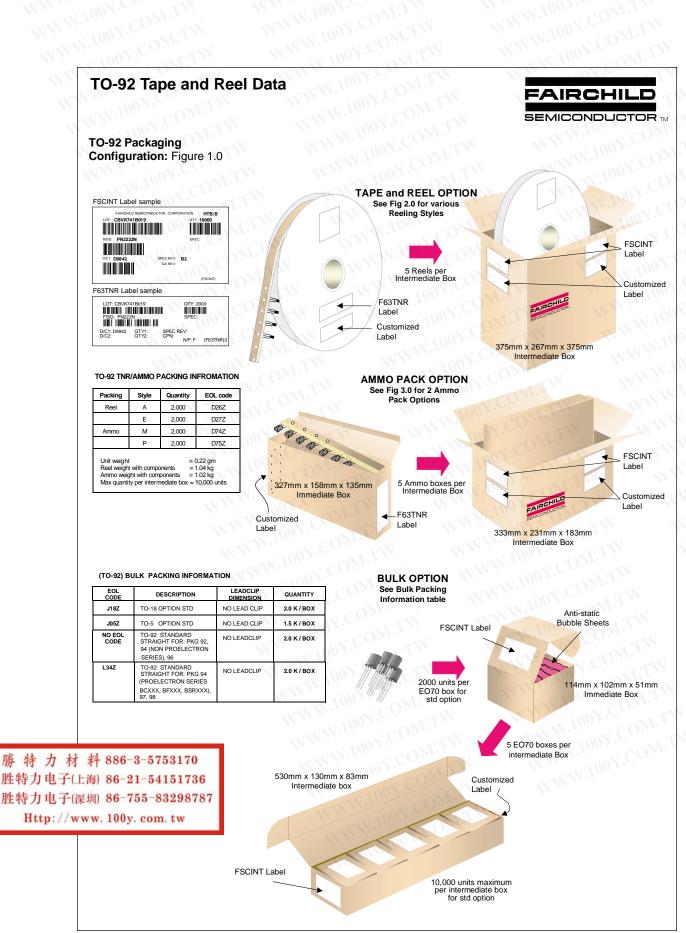


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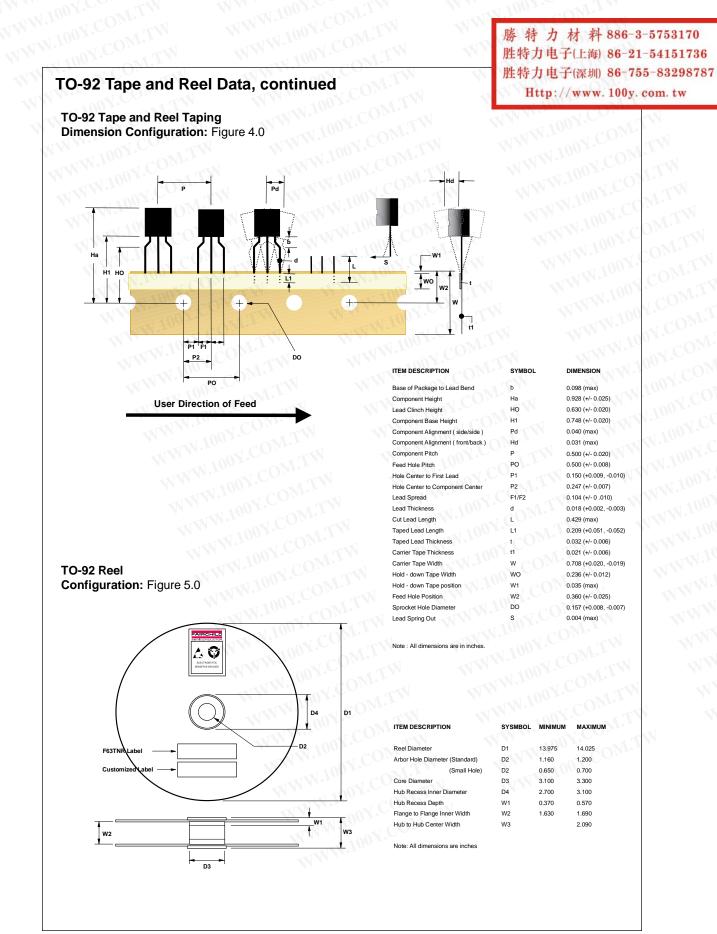
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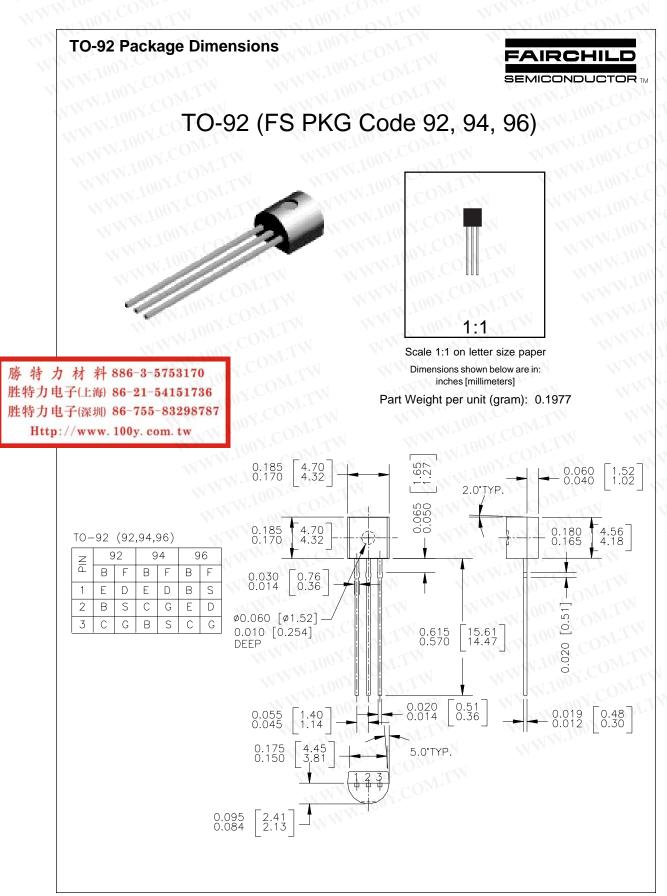


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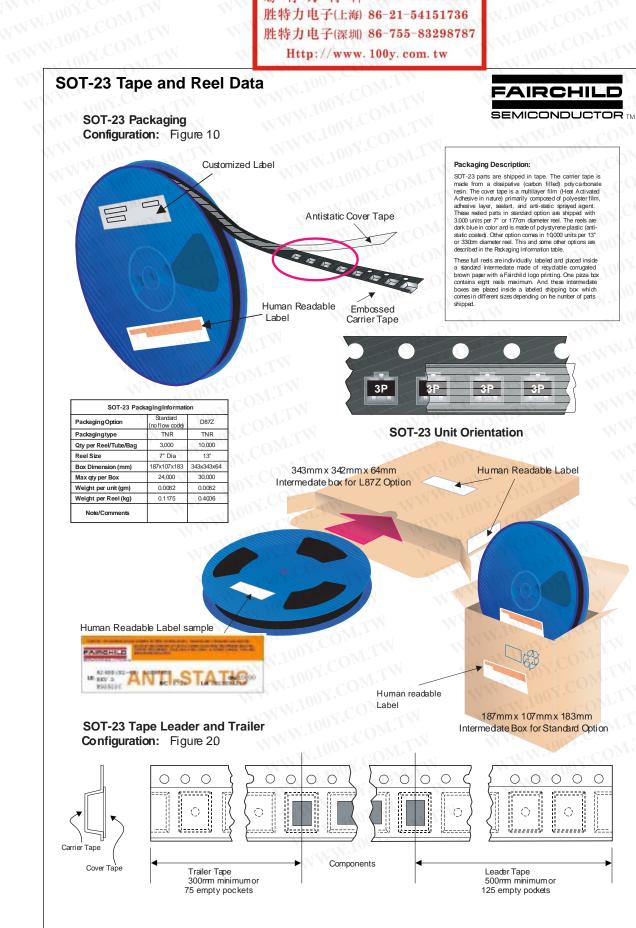
WWW.100Y.COM.TW WWW.100Y.COM.TW 特力材料 886-3-5753170 100X.COM.TW 100Y.COM.TW 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw TO-92 Tape and Reel Data, continued WWW.100Y.COM.TW WW.100Y.COM.TW **TO-92 Reeling Style Configuration:** Figure 2.0 Machine Option "A" (H) Machine Option "E" (J) 0 8 8 8 8 Y.COM.TW WW.100 DY.COM.TW Style "E", D27Z, D71Z (s/h) Style "A", D26Z, D70Z (s/h) WWW.100 WWW.10 **TO-92 Radial Ammo Packaging** W.100Y.COM Configuration: Figure 3.0 FIRST WIRE OFF IS COLLECTOR ADHESIVE TAPE IS ON THE TOP SIDE FLAT OF TRANSISTOR IS ON TOP FIRST WIRE OFF IS EMITTER ADHESIVE TAPE IS ON THE TOP SIDE FLAT OF TRANSISTOR IS ON BOTTOM 00 ORDER STYLE **ORDER STYLE** D74Z (M) D75Z (P) a a a a " **(**) 6 FIRST WIRE OFF IS EMITTER (ON PKG. 92) WWW.100Y.COM FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE WWW.100Y.COM.TW ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM FLAT OF TRANSISTOR IS ON TOP WWW.100Y.COM WWW.100Y.COM.T September 1999, Rev. B

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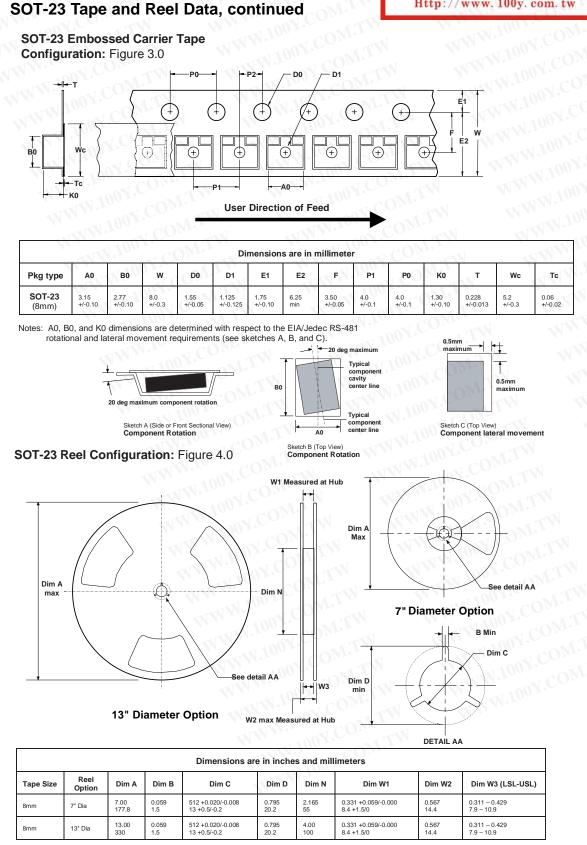






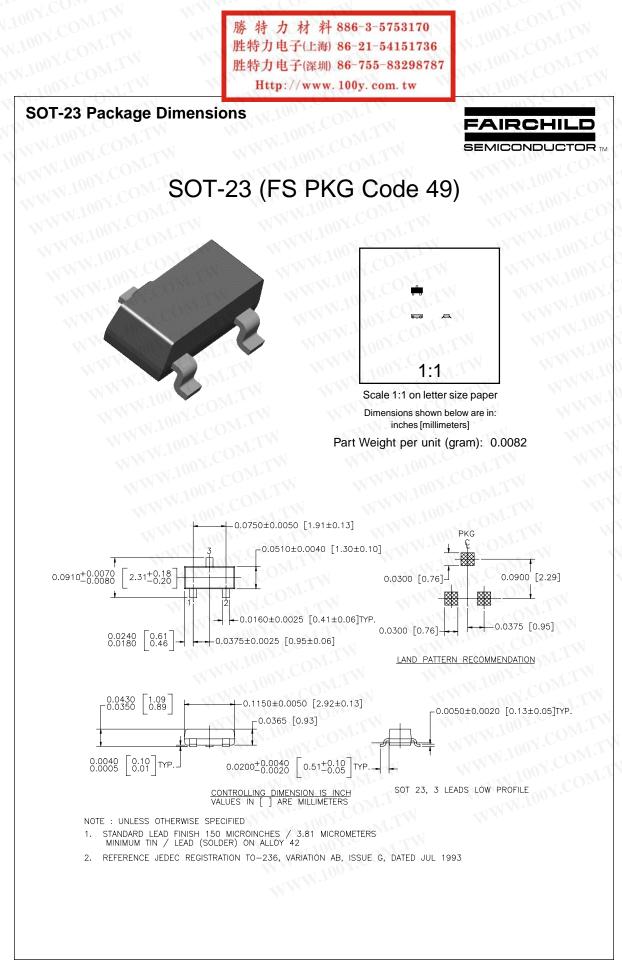
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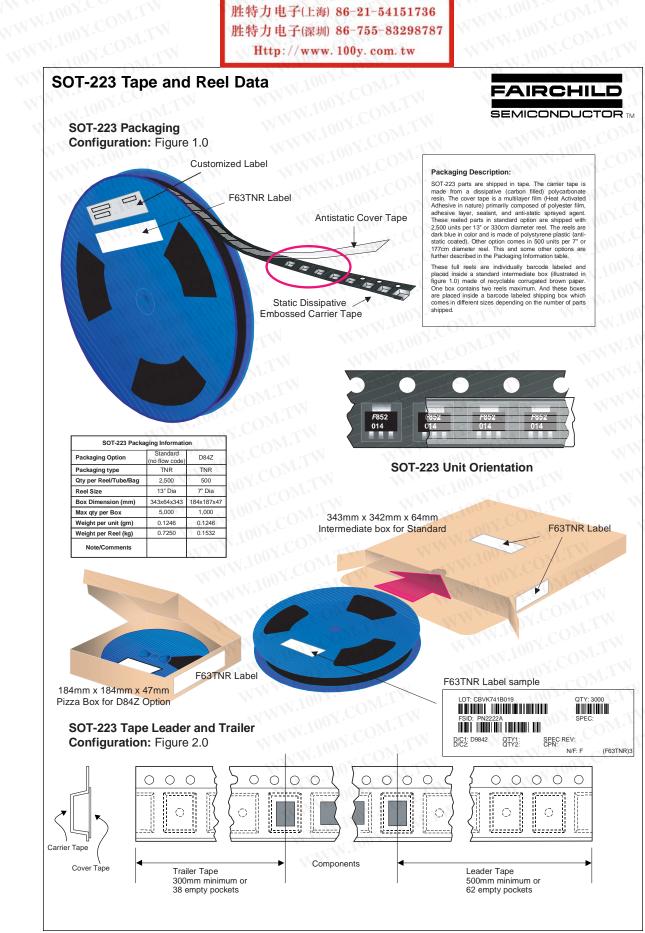
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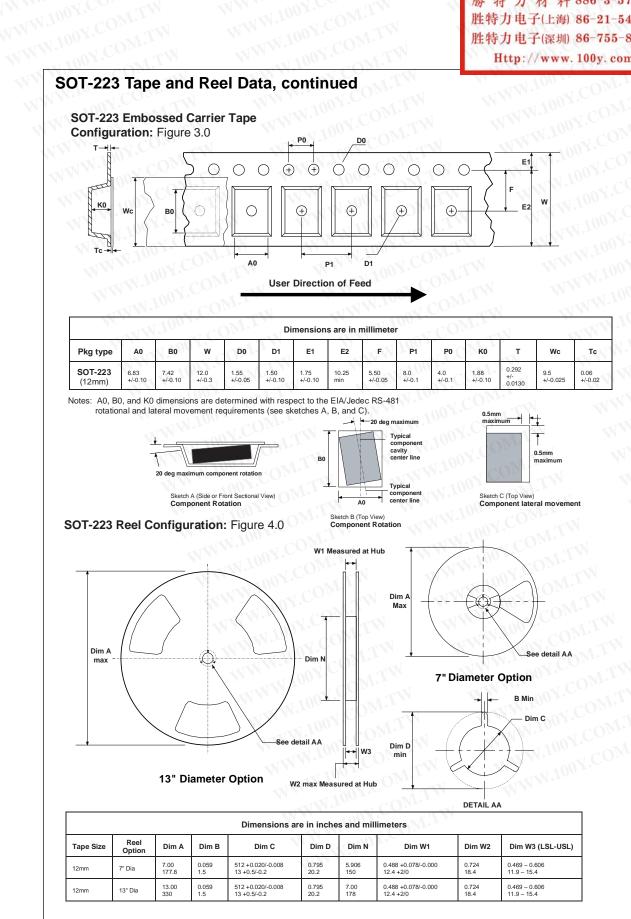
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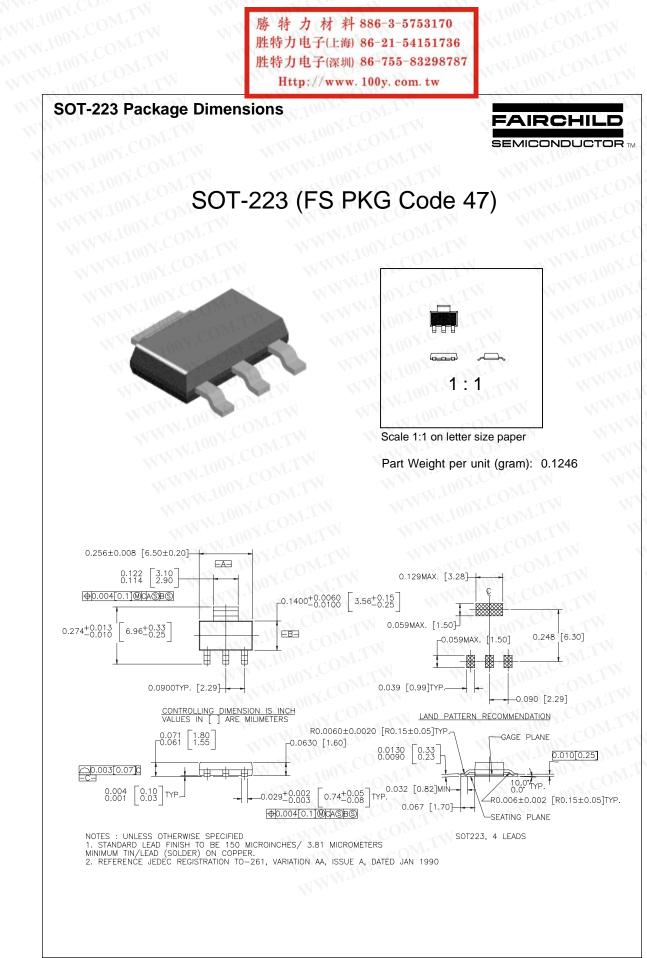
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